

# Zhongda Li

## List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

20  
papers

221  
citations

8  
h-index

14  
g-index

22  
ext. papers

251  
ext. citations

1.5  
avg, IF

3.1  
L-index

#	Paper	IF	Citations
20	Design and Simulation of 500-kV GaN Enhancement-Mode Vertical Superjunction HEMT. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 3230-3237	2.9	50
19	Sidewall Dominated Characteristics on Fin-Gate AlGaIn/GaN MOS-Channel-HEMTs. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 3025-3031	2.9	48
18	Impact of annealing on ALD Al <sub>2</sub> O <sub>3</sub> gate dielectric for GaN MOS devices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 907-910		28
17	Channel scaling of hybrid GaN MOS-HEMTs. <i>Solid-State Electronics</i> , <b>2011</b> , 56, 111-115	1.7	20
16	MetalOxideSemiconductor Interface and Dielectric Properties of Atomic Layer Deposited SiO <sub>2</sub> on GaN. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JN24	1.4	17
15	High voltage normally-off GaN MOSC-HEMTs on silicon substrates for power switching applications <b>2012</b> ,		10
14	Comparative study of 4H-SiC and 2H-GaN MOS capacitors and FETs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2009</b> , 206, 2478-2486	1.6	9
13	Drift region optimization in high-voltage GaN MOS-gated HEMTs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 2436-2438		8
12	Enhancement-mode GaN hybrid MOS-HEMTs with breakdown voltage of 1300V. <i>Power Semiconductor Devices &amp; ICs, 2009 ISPSD 2009 21st International Symposium on</i> , <b>2009</b> ,		6
11	Avalanche Breakdown Design Parameters in GaN. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JN05	1.4	5
10	Over 1000 V/30 mA operation GaN-on-Si MOSFETs fabricated on Si substrates. <i>Solid-State Electronics</i> , <b>2011</b> , 56, 73-78	1.7	5
9	Design and simulations of novel enhancement-mode high-voltage GaN vertical hybrid MOS-HEMTs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 1944-1948		4
8	Design and Simulation of Novel Enhancement Mode 500 kV GaN Vertical Superjunction High Electron Mobility Transistors for Smart Grid Applications. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JN01	1.4	3
7	Design of GaN and SiC 500kV vertical superjunction structures <b>2012</b> ,		2
6	Modeling and experimental study of MOS channel mobility of etched GaN on silicon substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 2433-2435		2
5	Experimental Identification of Extra Type of Charges at SiO <sub>2</sub> /SiC Interface in 4H-SiC. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 519-522	0.4	2
4	A New Method to Modify Two-Dimensional Electron Gas Density by GaN Cap Etching. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JN11	1.4	1

- 3 DC breakdown and TDDB study of ALD SiO<sub>2</sub> on GaN **2012**, 1
- 2 Study of CF<sub>4</sub> plasma treatment in drift region optimization of high-voltage GaN MOSC-HEMTs.  
*Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 861-863
- 1 Study of High Temperature Microwave Annealing on the Performance of 4H-SiC MOS Capacitors.  
*Materials Science Forum*, **2012**, 717-720, 769-772 0.4